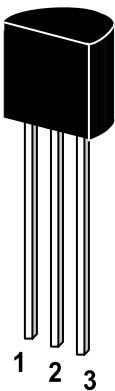


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PNP Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

On special request, these transistors can be
manufactured in different pin configurations.

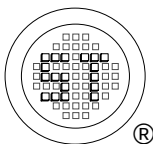


1. Emitter 2. Base 3. Collector

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	350	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	350	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current	$-I_{\text{C}}$	500	mA
Base Current	$-I_{\text{B}}$	250	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_{j}	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{s}	-55 to +150	$^{\circ}\text{C}$



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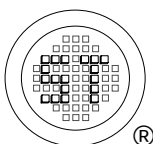
Dated : 07/12/2002

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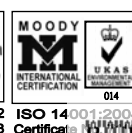
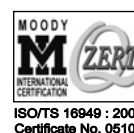
Characteristics at $T_{amb}=25^{\circ}C$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE}=10V$, $-I_C=1mA$	h_{FE}	20	-	-	-
at $-V_{CE}=10V$, $-I_C=10mA$	h_{FE}	30	-	-	-
at $-V_{CE}=10V$, $-I_C=30mA$	h_{FE}	30	-	200	-
at $-V_{CE}=10V$, $-I_C=50mA$	h_{FE}	20	-	200	-
at $-V_{CE}=10V$, $-I_C=100mA$	h_{FE}	15	-	-	-
Collector Base Breakdown Voltage					
at $-I_C=100\mu A$	$-BV_{CBO}$	350	-	-	V
Collector Emitter Breakdown Voltage					
at $-I_C=1mA$	$-BV_{CEO}$	350	-	-	V
Emitter Base Breakdown Voltage					
at $-I_E=10\mu A$	$-BV_{EBO}$	5	-	-	V
Collector Cutoff Current					
at $-V_{CB}=250V$	$-I_{CBO}$	-	-	50	nA
Emitter Cutoff Current					
at $-V_{EB}=4V$	$-I_{EBO}$	-	-	50	nA
Collector Base Capacitance					
at $-V_{CB}=20V$, $f=1MHz$	C_{cb}	-	-	6	pF
Emitter Base Capacitance					
at $-V_{EB}=0.5V$, $f=1MHz$	C_{eb}	-	-	100	pF
Base Emitter Saturation Voltage					
at $-I_C=10mA$, $-I_B=1mA$	$-V_{BE(sat)}$	-	-	0.75	V
at $-I_C=20mA$, $-I_B=2mA$	$-V_{BE(sat)}$	-	-	0.85	V
at $-I_C=30mA$, $-I_B=3mA$	$-V_{BE(sat)}$	-	-	0.9	V
Collector Emitter Saturation Voltage					
at $-I_C=10mA$, $-I_B=1mA$	$-V_{CE(sat)}$	-	-	0.3	V
at $-I_C=20mA$, $-I_B=2mA$	$-V_{CE(sat)}$	-	-	0.35	V
at $-I_C=30mA$, $-I_B=3mA$	$-V_{CE(sat)}$	-	-	0.5	V
at $-I_C=50mA$, $-I_B=5mA$	$-V_{CE(sat)}$	-	-	1	V
Base Emitter On Voltage					
at $-V_{CE}=10V$, $-I_C=100mA$	$-V_{BE(on)}$	-	-	2	V
Current Gain Bandwidth Product					
at $-V_{CE}=20V$, $-I_C=10mA$, $f=20MHz$	f_T	40	-	200	MHz
Turn On Time					
at $-V_{BE(off)}=2V$, $-V_{CC}=100V$ $-I_C=50mA$, $-I_{B1}=10mA$	t_{on}	-	-	200	ns
Turn Off Time					
at $-V_{CC}=100V$, $-I_C=50mA$, $-I_{B1}=-I_{B2}=10mA$	t_{off}	-	-	3.5	ns



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